REMARKS

By the present amendment, claim 1 has been amended to further clarify the concepts of the present invention. More particularly, claim 1 has been amended to incorporate the subject matter of dependent claim 2 therein and claim 2 has been cancelled. New independent claim 3 and dependent claims 4-6 have also been added. Entry of these amendments is respectfully requested.

In the Action, claims 1 and 2 were rejected under 35 USC § 103(a) as being unpatentable over the publication to Steckl et al published in IEEE Transactions in view of the patent to Steckl et al. In making this rejection, it basically was asserted that the publication teaches the entire manufacturing apparatus as set forth in the noted claims except for teaching that the substrate is a SOI substrate of the recited characteristics. The patent to Steckl et al was then asserted to provide this teaching deficiency in terms of a SOI substrate. Reconsideration of this rejection in view of the above claim amendments and the following comments is respectfully requested.

It is submitted that the manufacturing apparatus of a buried insulating layer-type semiconductor silicon carbide substrate as defined by independent claim 1 as amended herein and newly added independent claim 3 are not taught or suggested by the cited publication to Steckl et al and the patent to Steckl et al, whether taken singly or in

combination. Among other things, these publications do not teach or suggest a manufacturing apparatus of a buried insulating layer-type semiconductor silicon carbide substrate as defined by independent claims 1 and 3 which is operated at atmospheric pressure.

According to the art as exemplified by the Steckl et al publication and the Steckl et al patent, a series of processes for fabricating semiconductors are conducted inside a chamber maintained in a vacuum. It is clear that maintaining the chamber under vacuum will cause the fabrication apparatus itself to be large in size as well as complicated in configuration.

In distinct contrast, the apparatus of the presently claimed invention includes the feature that a series of processes for forming a single crystal silicon carbide thin layer are conducted inside a chamber at atmospheric pressure. Exhaust means is provided exclusively for maintaining the inside of the heating furnace at the atmospheric pressure. Since the inside of the heating furnace is not required to be under a vacuum, hence the claimed apparatus itself can be downsized and simplified, in contrast to the above art, and is an advantageous feature of the apparatus of the presently claimed invention.

For the reasons stated above, withdrawal of the rejection under 35 U.S.C. § 103(a) and allowance of claim 1 as amended and claims 3 through 6 as added over the cited

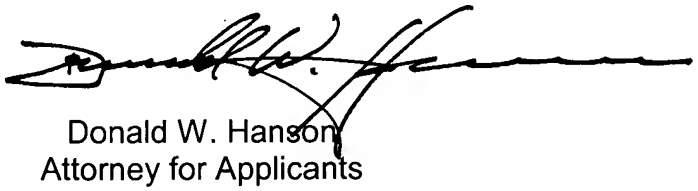
publications are respectfully requested.

In view of the foregoing, it is submitted that the subject application is now in condition for allowance and early notice to that effect is earnestly solicited.

In the event this paper is not timely filed, the undersigned hereby petitions for an appropriate extension of time. The fee for this extension may be charged to Deposit Account No. 01-2340, along with any other additional fees which may be required with respect to this paper.

Respectfully submitted,

ARMSTRONG, KRATZ, QUINTOS, HANSON & BROOKS, LLP



Donald W. Hanson
Attorney for Applicants
Reg. No. 27,133

Atty. Docket No. 021740A
Suite 1000, 1725 K Street, N.W.
Washington, D.C. 20006
(202) 659-2930
DWH/nk

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PATENT TRADEMARK OFFICE